Abstracts

The Development of High-Power, Low-Frequency PIN Diodes

M. Caulton, A. Rosen, P. Stabile and A. Gombar. "The Development of High-Power, Low-Frequency PIN Diodes." 1981 MTT-S International Microwave Symposium Digest 81.1 (1981 [MWSYM]): 255-257.

The application of PIN diodes in high-power systems at frequencies as low as 500 kHz requires the use of diodes with intrinsic layers of long carrier lifetimes, operation at low rf-to-bias current ratios, and large reverse bias voltages. The development of suitable diodes, operating conditions, and test results in actual circuits are described.

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